

<b>BT134</b>		
	双向可控硅 TRIAC	版本号 201603-A

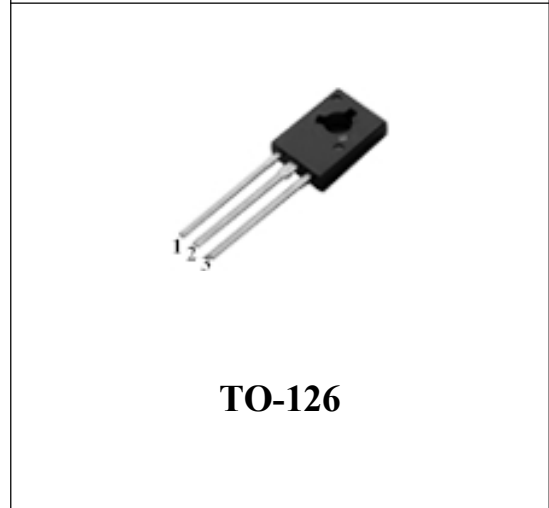
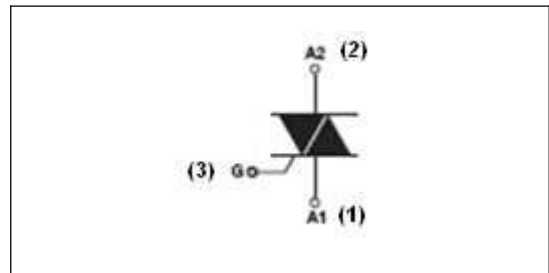
## 产品概述 GENERAL DESCRIPTION

BT134 双向可控硅采用穿通隔离台面结构，复合玻璃钝化PN结表面保护工艺技术，dv/dt高，可靠性高，适用于控温、调光、马达控制。

BT134 Triacs is fabricated using separation diffusion processes ,the junction termination areas are passivated with glass. Thanks to highly dv/dt and reliability,the Triacs series is suitable for domestic lighting ,heating and motor speed controllers.

## 主要参数 MAIN CHARACTERISTICS

参数 Parameter	数值 Value	单位 Unit
$I_{T(RMS)}$	4	A
$V_{DRM}/V_{RRM}$	600&800	V
$I_{GT(III)}$	$\leq 25$	mA



## 产品特性 FEATURES

- |   |   |
|---|---|
| <ul style="list-style-type: none"> <li>● dv/dt高</li> <li>● 通态压降低</li> <li>● Rohs环保产品</li> </ul> | <ul style="list-style-type: none"> <li>● Highly dv/dt</li> <li>● Low on-state voltage</li> <li>● Rohs Products</li> </ul> |
|---|---|

## 应用领域 APPLICATIONS

主要应用于调光、控温、马达控制。

domestic lighting ,heating and motor speed controllers.

## 极限值(除非另有规定, T<sub>j</sub>=25°C) ABSOLUTE RATINGS

(T<sub>j</sub>=25°C, unless otherwise specified)

符号 Symbol	参数 Parameter	数值 Value	单位 Unit
I <sub>T(RMS)</sub>	RMS 通态电流 RMS on-state current (full sine wave)	T <sub>C</sub> ≤107°C	4 A
I <sub>TSM</sub>	通态峰值浪涌电流 Non repetitive surge peak on-state current	F=50Hz, t=20ms	25 A
I <sup>2</sup> t	I <sup>2</sup> t 耗散值 I <sup>2</sup> t value for fusing	T <sub>P</sub> =10ms	3.1 A <sup>2</sup> s
di/dt	通态电流上升值 Critical rate of rise of on-state current	F=120Hz, T <sub>j</sub> =125°C	50 A/μs
I <sub>GM</sub>	门极峰值电流 Peak gate current	T <sub>P</sub> =20μs, T <sub>j</sub> =125°C	2 A
P <sub>G(AV)</sub>	平均门极耗散功率 Average gate power dissipation	T <sub>j</sub> =125°C	0.5 W
T <sub>stg</sub>	贮存结温范围 Storage junction temperature range		-40~+150 °C
T <sub>j</sub>	工作结温范围 Operating junction temperature range		-40~+125 °C

## 电参数(除非另有规定, T<sub>j</sub>=25°C) ELECTRICAL CHARACTERISTICS

(T<sub>j</sub>=25°C, unless otherwise specified)

参数 Parameter	符号 Symbol	规范值	Value	单位 Unit	测试条件 Test Conditions
		D	E		
触发电流 Gate trigger current	I <sub>GT</sub>	I ~ III	5	10	mA V <sub>D</sub> =12V, I <sub>T</sub> =0.1A
		IV	10	25	
触发电压 Gate trigger voltage	V <sub>GT</sub>	I ~ IV	≤1.5		V V <sub>D</sub> =12V, I <sub>T</sub> =0.1A
维持电流 Holding current	I <sub>H</sub>		10	20	mA V <sub>D</sub> =12V, I <sub>T</sub> =0.1A
擎住电流 Latching current	I <sub>L</sub>	I、III	10	15	mA V <sub>D</sub> =12V, I <sub>T</sub> =0.1A
		II、IV	15	20	
电压上升率 Rise of off- state voltage	dv/dt		5	50	V/μS V <sub>D</sub> =67%V <sub>DRM</sub>
通态压降 Peak on-state voltage	V <sub>TM</sub>		1.7		V I <sub>T</sub> =5.5A
断态漏电流 Peak repetitive forward blocking current	I <sub>DRM</sub> I <sub>RRM</sub>		5		μA V <sub>RRM</sub> =V <sub>DRM</sub> , T <sub>j</sub> =25°C
			0.8		mA V <sub>RRM</sub> =V <sub>DRM</sub> , T <sub>j</sub> =125°C

## 热特性 THERMAL RESISTANCES

符号 Symbol	参数 Parameter	数值 Value	单位 Unit
R <sub>th(j-c)</sub>	Junction to case(AC)	4.1	K/W
R <sub>th(j-a)</sub>	Junction to ambient	100	K/W

特征曲线 ELECTRICAL CHARACTERISTICS (CURVES)

图1 最大耗散功率与RMS通态电流关系

Fig.1.Maximum Power Dissipation Versus on-state current

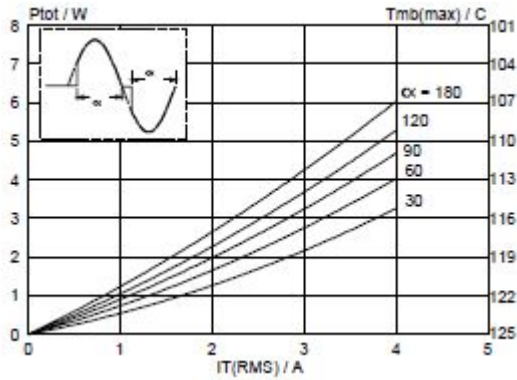


图3 通态特性

Fig.3.On-State Characteristics

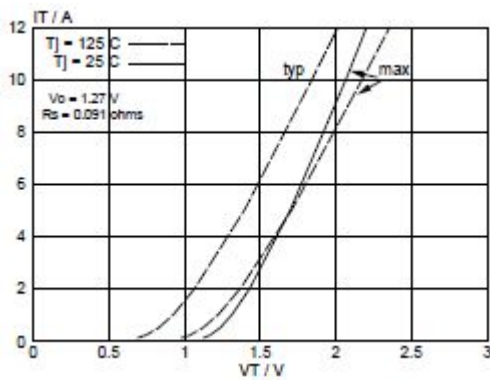


图2 RMS通态电流与Tc温度关系

Fig.2. RMS On-state Current Versus TL

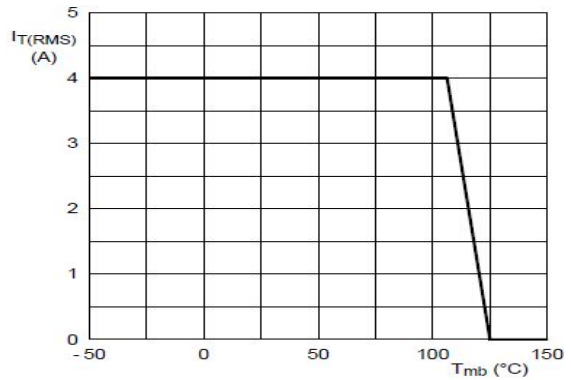


图4 通态浪涌峰值电流与周期数关系

Fig.4.Surge Peak On-state Current Versus Number Cycles

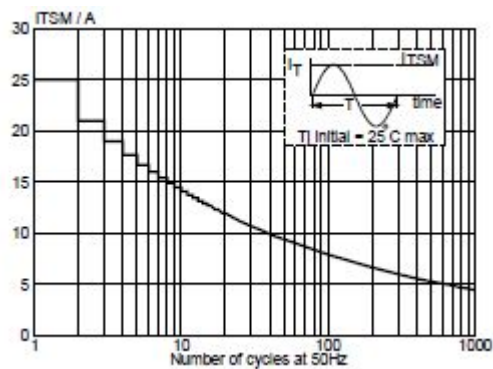
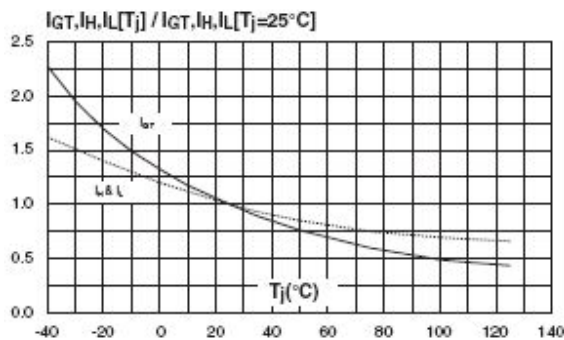


图5 IGT、IH、IL相对值（相对于25°C）与结温关系

Fig.5.Relative Variation Of Gate Trigger Current , Holding Current And Latching Current Versus Junction Temperature (Typical Value)

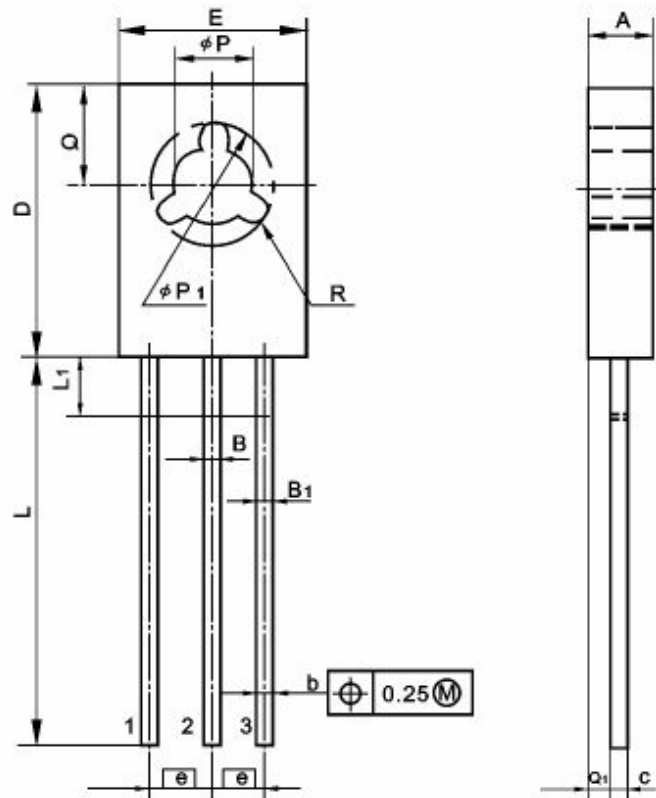


封装尺寸 PACKAGE MECHANICAL DATA

TO-126

UNIT: mm

SYMBOL	min	nom	max	SYMBOL	min	nom	max
A	2.3		2.8	L	15.3		16.5
B	1.0		1.2	L1			2.54
B1	0.8		1.0	$\phi P$	3.0		3.2
b	0.65		0.88	$\phi P1$		5.0	
c	0.45		0.60	Q	3.6		4.4
D	10.5		11.1	Q1	0.9		1.5
E	7.2		7.8	R		0.5*	
e		2.29					



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